

VSI Specifications for SOI Wafers

Bonded Wafer Specifications

Wafer Properties

Target Specifications

Thermal SiO₂ Layer Thickness	0.5μm – 4.0μm
Handle Wafer Thickness	250μm – 1000μm
Device Wafer Thickness	10μm – 525μm
Device Wafer Tolerance	0.5μm – 25μm
Device and Handle Wafer Resistivities	0.01 – 100.0 Ohm-cm
Crystal Orientation & Dopant	ANY
Wafer Diameter	100mm & 150mm